TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

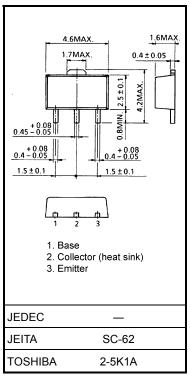
2SC4540

Power Amplifier Applications Power Switching Applications

- Low saturation voltage: VCE (sat) = 0.5 V (max) (IC = 500 mA)
- High speed switching time: $t_{stg} = 0.4 \ \mu s \ (typ.)$
- Small flat package
- PC = 1.0 to 2.0 W (mounted on a ceramic substrate)
- Complementary to 2SA1735

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	80	V	
Collector-emitter voltage	V _{CEO}	50	V	
Emitter-base voltage	V _{EBO}	6	V	
Collector current	Ι _C	1	А	
Base current	Ι _Β	0.2	А	
Collector power dissipation	P _C	500	mW	
Collector power dissipation	P _C (Note)	1000	mW	
Junction temperature	Тj	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	



Weight: 0.05 g (typ.)

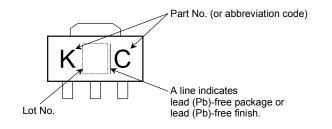
Note: Mounted on a ceramic substrate (250 mm² × 0.8 t)

Unit: mm

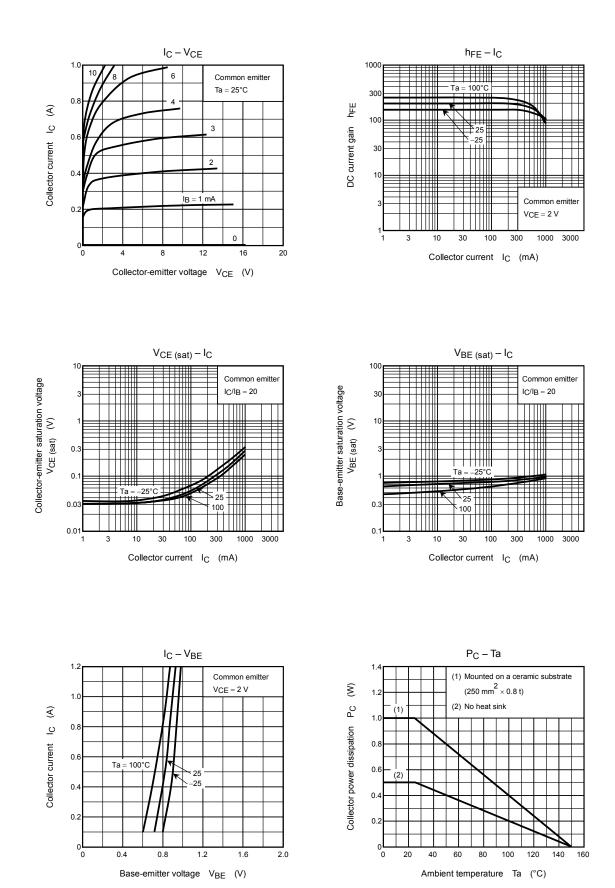
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off cu	ırrent	I _{CBO}	V _{CB} = 80 V, I _E = 0	_	—	0.1	μA
Emitter cut-off current		I _{EBO}	V _{EB} = 6 V, I _C = 0		_	0.1	μA
Collector-emitter b	reakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	50	_	_	V
DC current gain		h _{FE (1)}	V _{CE} = 2 V, I _C = 100 mA	120	_	400	
		h _{FE (2)}	V _{CE} = 2 V, I _C = 700 mA	40	_	_	
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 500 mA, I _B = 25 mA		_	0.5	V
Base-emitter saturation voltage		V _{BE (sat)}	I _C = 500 mA, I _B = 25 mA		_	1.2	V
Transition frequency		f _T	V _{CE} = 2 V, I _C = 100 mA		100	_	MHz
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz		10	_	pF
Switching time	Turn-on time	t _{on}	OUTPUT 20 μ s INPUT B_1 B_1 B_1 B_2 B_1 B_2 B_1 B_2 B_2 B_2 B_1 B_2 B_2 B_2 B_1 B_2 B_3 B_4	_	0.1	_	
	Storage time	t _{stg}		_	0.4	_	μs
	Fall time	t _f		_	0.1	_	

Marking



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